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Kind regards,

Team Nexperia



RB521S30

200 mA low V_F MEGA Schottky barrier rectifier Rev. 01 — 6 October 2009

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

Average forward current: I_{F(AV)} ≤ 0.2 A

Reverse voltage: V_R ≤ 30 V

■ Low reverse current: $I_R \le 30 \mu A$

AEC-Q101 qualified

Ultra small and flat lead SMD plastic package

1.3 Applications

- Low current rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. **Quick reference data** $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz				
		T _{amb} ≤ 120 °C	<u>[1]</u> _	-	0.2	Α
		$T_{sp} \le 140 ^{\circ}C$	-	-	0.2	Α
I_R	reverse current	$V_R = 10 V$	-	2.5	30	μΑ
V_R	reverse voltage		-	-	30	V
V_{F}	forward voltage	$I_F = 0.2 A$	[2] _	420	500	mV

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, mounting pad for cathode 1 cm².



^[2] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	<u>[1]</u>	
2	anode		1 - 2
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
RB521S30	SC-79	plastic surface-mounted package; 2 leads	SOD523

4. Marking

Table 4. Marking codes

Type number	Marking code
RB521S30	ZB

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	$T_j = 25 ^{\circ}C$	-	30	V
$I_{F(AV)}$	average forward current	square wave; δ = 0.5; f = 20 kHz			
		T _{amb} ≤ 120 °C	<u>[1]</u> _	0.2	Α
		T _{sp} ≤ 140 °C	-	0.2	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms half sine wave; JEDEC method	[2] _	1	A
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	275	mW
			[3][1]	420	mW
			[3][5]	500	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [2] $T_i = 25$ °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]			
		[3]	-	455	K/W	
			<u>[4]</u> -	-	300	K/W
			<u>[5]</u> _	-	250	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	90	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Soldering point of cathode tab.

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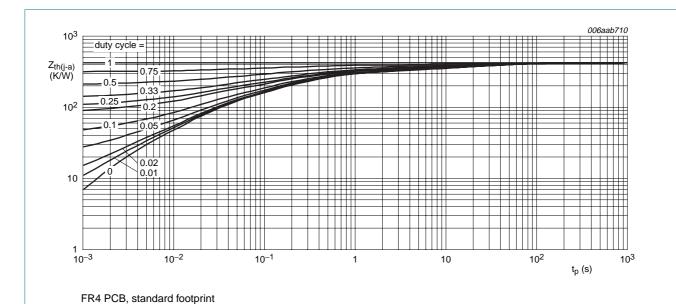


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

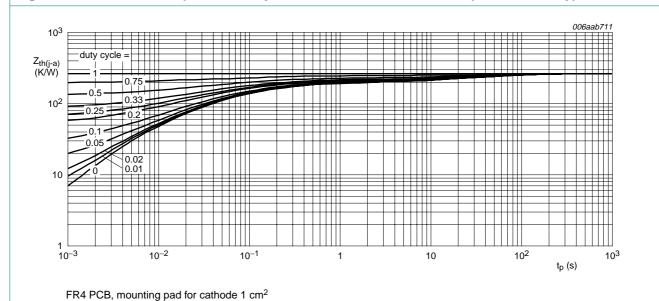


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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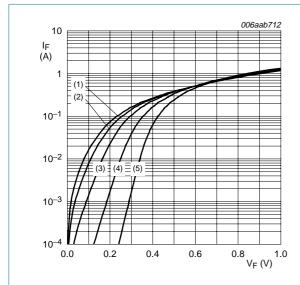
7. Characteristics

Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	V _F forward voltage		<u>[1]</u>			
	$I_F = 0.1 \text{ mA}$	-	130	190	mV	
		$I_F = 1 \text{ mA}$	-	190	250	mV
		$I_F = 10 \text{ mA}$	-	255	300	mV
		$I_F = 100 \text{ mA}$	-	355	410	mV
		$I_F = 200 \text{ mA}$	-	420	500	mV
I _R	reverse current	V _R = 10 V	-	2.5	30	μΑ
C _d	diode capacitance	$f = 1 MHz; V_R = 1 V$	-	20	25	pF

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$





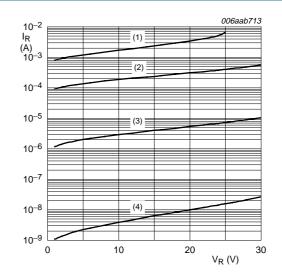
(2)
$$T_j = 125 \,^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_j = 25 \,^{\circ}\text{C}$$

(5)
$$T_j = -40 \, ^{\circ}C$$

Fig 3. Forward current as a function of forward voltage; typical values



(1) $T_j = 125 \,^{\circ}C$

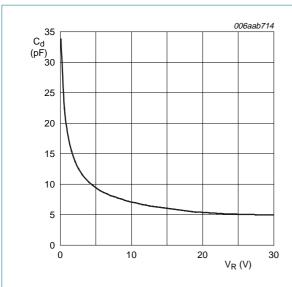
(2)
$$T_i = 85 \,^{\circ}\text{C}$$

(3)
$$T_i = 25 \, ^{\circ}C$$

(4)
$$T_j = -40 \, ^{\circ}C$$

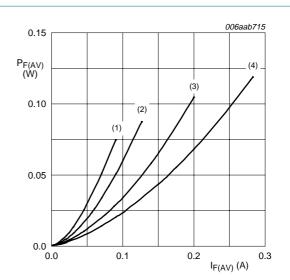
Fig 4. Reverse current as a function of reverse voltage; typical values

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 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

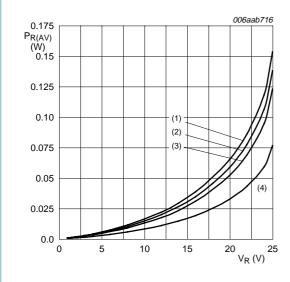
Fig 5. Diode capacitance as a function of reverse voltage; typical values



T_j = 150 °C

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

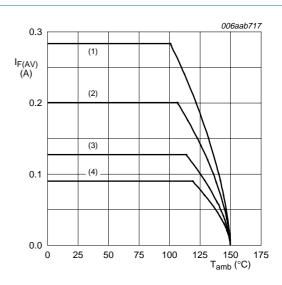
Fig 6. Average forward power dissipation as a function of average forward current; typical values



T_j = 125 °C

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

Fig 7. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

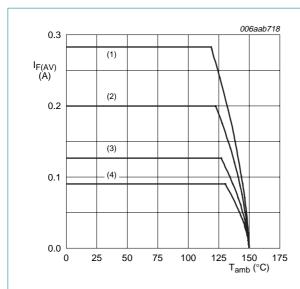
$$T_j = 150 \, ^{\circ}C$$

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 8. Average forward current as a function of ambient temperature; typical values

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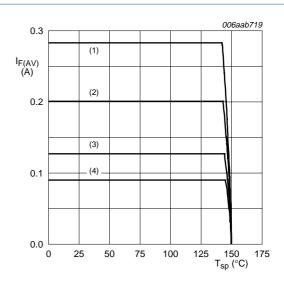
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FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

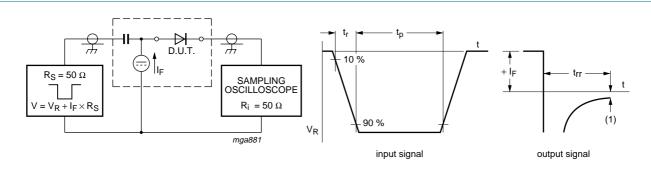
Fig 9. Average forward current as a function of ambient temperature; typical values



- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 10. Average forward current as a function of solder point temperature; typical values

8. Test information



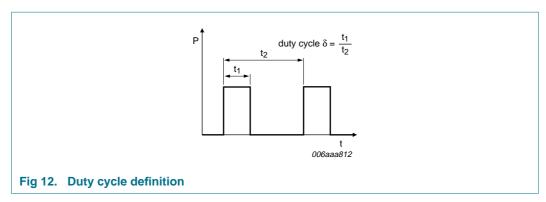
(1) $I_R = 1 \text{ mA}$

Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty cycle δ = 0.05 Oscilloscope: rise time t_r = 0.35 ns

Fig 11. Reverse recovery time test circuit and waveforms

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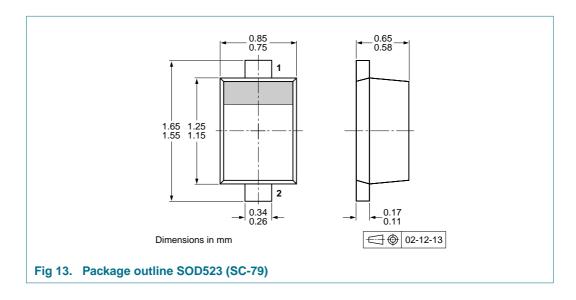


The current ratings for the typical waveforms as shown in Figure 8, 9 and 10 are calculated according to the equations: $I_{F(AV)}=I_M\times\delta$ with I_M defined as peak current, $I_{RMS}=I_{F(AV)}$ at DC, and $I_{RMS}=I_M\times\sqrt\delta$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



200 mA low V_F MEGA Schottky barrier rectifier

10. Packing information

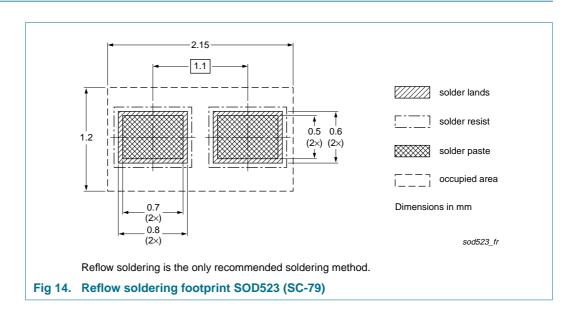
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number Package		Description	Packing quantity		
			3000	8000	10000
RB521S30	SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-
		4 mm pitch, 8 mm tape and reel	-115	-	-135

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
RB521S30_1	20091006	Product data sheet	-	-

200 mA low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Date of release: 6 October 2009

Document identifier: RB521S30_1